**Progress in Applied Surface, Interface  
   and Thin Film Science 2012**

**SURFINT-SREN III, 14-19. May 2012**

**Invited speakers**  
  
  
**� Dietrich R.T. Zahn, Chemnitz University of Technology, Chemnitz, Germany  
   Ferromagnetic/Organic Interfaces for Spintronic Applications  
  
� Hikaru Kobayashi, Institute of Scientific and Industrial Research and CREST,  
   Japan Science and Technology Agency, Osaka University, Japan  
   New surface technologies for improvement of conversion efficiencies of crystalline Si solar cells  
  
� Shigeru Masuda, Department of Basic Science, The University of Tokyo, Japan  
   A new characterization of electronic states at organic�metal interface  
  
� Toshiaki Makabe, Keio University, Yokohama, Japan  
   Influence of gas heating on a plasma structure in an rf-microcell in Ar  
  
� Thomas Chass�, Institute f�r Physikalische Chemie, Universit�t T�bingen, T�bingen, Germany  
   Electronic interactions at transition metal phthalocyanine - metal interfaces  
  
� Helena Gleskova, Department of Electronic and Electrical Engineering, University of Strathclyde,  
   Glasgow, United Kingdom  
   Ultra-thin, inorganic-organic dielectric bi-layers as gate dielectrics in organic thin-film transistors  
  
� Shigeki Imai, Institute of Scientific and Industrial Research and CREST,  
   Japan Science and Technology Agency, Osaka University, Japan  
   Thin Film Transistors (TFT) with Stacked Gate Oxide Formed by the Nitric Acid Oxidation of Si  
   (NAOS) Method and Application to Low Power Liquid Crystal Display (LCD) and Ring Oscillator  
  
� Taketoshi Matsumoto, Institute of Scientific and Industrial Research and CREST,  
   Japan Science and Technology Agency, Osaka University, Japan  
   Application of Ultra-thin SiO2 Layer Formed by the Nitric Acid Oxidation of Si  
   (NAOS) Method to Stacked Gate Oxide in Thin Film Transistors (TFT)  
  
� Heike Angermann, Helmholtz-Zentrum f�r Materialien und Energie GmbH,  
   Institute f�r Silizium-Photovoltaik, Berlin, Germany  
   Interface states and recombination losses on textured Si substrates after wet-chemical  
   conditioning  
  
� Jozef Nov�k, Institute of Electrical Engineering SAS, Bratislava, Slovakia  
   ZnO/GaP Nanowires Prepared by Combination of MOVPE growth and RF sputtering  
  
� �tefan Chromik, Institute of Electrical Engineering SAS, Bratislava, Slovakia  
   Significant increasing of onset temperature of FM transition in LSMO thin films  
  
� Giovanni Piero Pepe, Universita di Napoli �Federico II�, Napoli, Italy  
   Self-assembled plasmonic arrays based on block-copolymer nanostructures:  
   transport and optical properties  
  
� Roman Sobolewski, University of Rochester, Rochester, USA, and  
   Institute of Electron Technology, Warsaw, Poland  
   Femtosecond time-resolved studies of carrier and spin dynamics in all-oxide  
   superconductor/ferromagnet proximitized nanobilayers  
  
� Zsolt Jozsef Horv�th, �buda University and Research Institute for  
   Technical Physics and Materials Science HAS, Budapest, Hungary  
   Silicon nitride based non-volatile memory structures with embedded  
   semiconductor nanocrystals  
  
� Katsuhiro Akimoto, Tsukuba University, Tsukuba, Ibaraki, Japan  
   Non-radiative recombination centers in Cu(In,Ga)Se2  
  
� Kazuyuki Edamoto, Rikkyo University, Toshima, Tokyo, Japan  
   The electronic properties of transition metal phosphide surfaces:  
   Angle-resolved and resonant photoemission studies  
  
� Peter �vec, Institute of Physics SAS, Bratislava, Slovakia  
   Formation, structure and properties of mono, bi and tri-layered rapidly quenched ribbons  
  
� Aarne Kasikov, Institute of Physics, University of Tartu, Tartu, Estonia  
   Transmission spectrometry vs spectral ellipsometry: Bruggeman EMA layer revisited  
  
� Ratiba Outemzabet, Universite des Sciences et de la Technologie Honari Boumedienne,  
   Alger, Alg�ria  
   Competition and transition between oxides and silicon hydrides at anodised Silicon/HF interface  
  
� Yossi Paltiel, Faculty of Science, The Hebrew University, Jerusalem, Israel  
   Quantum Devices Using Monolayer Hybrid Surfaces  
  
� Sabu Thomas, Centre for Nanoscience and Nanotechnology, School of Chemical Sciences,  
   Mahatma Gandhi University, Kottayam, Kerala, India  
   Micro and Nanostructured Epoxy based Blends for Supertoughnes  
  
� Stanislav Jure�ka, University of �ilina, Slovak Republic  
   Physics-based models for evaluating of MOS capacitors with ultrathin oxide layer  
  
� Uros Cvelbar, Jozef Stefan Institute, Ljubljana, Slovenia  
   Large scale production of metal-oxide nanowires for next step  
  
� Jaroslav Kov��, Faculty of Electrical Engineering and Information Technology,  
   Institute of Electronics and Photonics of Slovak University of Technology, Bratislava,  
   Slovak Republic  
   Micro Raman spectroscopy diagnostics of semiconductor structures and devices  
  
� Amarjeet Kaur, Department of Physics and Astrophysics, University of Delhi, Delhi, India  
   Donor-Acceptor nanoparticles interactions in the organic solar cell devices  
  
� Michal Ru�insk�, Institute of Power and Applied Electrical Engineering of FEEIT of SUT,  
   Bratislava, Slovak Republic  
   History and the Present Time of Solar Car Races in the World  
  
� Renato S. Gonnelli, Dipartimento di Scienza Applicata e Tecnologia, Politecnico di Torino,  
   Torino, Italy  
   Huge field-effect surface charge injection and conductance modulation in metal thin films by  
   electrochemical gating  
  
� Jun Xu, Department of Microelectronics and Optoelectronics, School of Electronic Science and  
   Engineering, Nanjing University, Nanjing, China  
   Preparation of size-controllable Si quantum dot multilayers for photonic and photovoltaic  
   applications  
  
� Pavel �utta, New Technologies - Research Center, University of West Bohemia, Plze�,  
   Czech Republic  
   Microstructure determination of microcrystalline-Si:H films analysing the breadths of  
   diffraction and spectral lines of XRD, FTIR and Raman spectroscopies  
  
� Vitaly L. Alperovich, Institute of Semiconductor Physics, Novosibirsk, Russia  
   Atomic smoothing of GaAs surface in equilibrium conditions  
  
� Cesare Frigeri, CNR-IMEM Institute, Parma, Italy  
  
� Benoit Jouault, CNRS, Universit� Montpellier, Montpellier, France  
   Surface graphene films on SiC with application to the metrology of quantum resistances  
  
� Alexander �atka, FEEIT Slovak University of Technology, Bratislava, Slovak Republic  
   EBIC at Schottky nanocontact on GaN epitaxial layers**